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Terms: **59257686** ([Edit Search](#))

JP-A 61136262; JP-A 59257686; JP-A 84257686

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PATENT ABSTRACTS OF JAPAN

61136262

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June 24, 1986

SOLID-STATE IMAGE PICKUP DEVICE AND MANUFACTURE THEREOF

INVENTOR: AZUMA AKIO; KAWAJIRI KAZUHIRO; SHINADA HARUJI; TAMURA HIROSHI;
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APPL-NO: 59257686 (JP 84257686)

FILED: December 7, 1984

ASSIGNEE: FUJI PHOTO FILM CO LTD

INT-CL: H01L27/14, (Section H, Class 01, Sub-class L, Group 27, Sub-group 14); H04N5/30,
(Section H, Class 04, Sub-class N, Group 5, Sub-group 30)

ABST:

PURPOSE: To prevent short circuits in a photoconductive layer due to erosion during an etching process accomplished to divide the photoconductive layer into picture elements by a method wherein a first transparent electrode layer is formed on an photosensitive layer and a second transparent electrode layer is formed with the intermediary of an interlayer insulating film.

CONSTITUTION: A scanning circuit substrate 100 is provided with a MOS field effect transistor constituted of a source 1, drain 2 and gate 3. An electrode 6, insulating layer 7 and groundwork electrode 8 are added. An N type and P<+> type amorphous silicon films 9, 10 are formed, which is followed by the provision of a protecting first transparent electrode layer 11 composed of ITO, SnO[3], In[2]O[3], CdO[2], CrSix, or the like, which is further followed by the formation of a photoconductive film section 200. Etching is accomplished for the formation of an inter-element dividing groove 13 is formed, and PSG, polyimide, or the like is attached to serve as an inter-layer insulating film 14. Selective etching is accomplished for the provision of an opening, wherein a second transparent electrode layer 16 is attached, whereon a metal-made optical shield layer 17 is formed in an inter-element dividing region composed materially similar to the transparent electrode layer 11. The transparent electrode layer protects a P<+> type amorphous silicon film that is a photosensitive layer from erosion.

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